File   View   Edit   Tools   Window   Help

- Pending
- Active
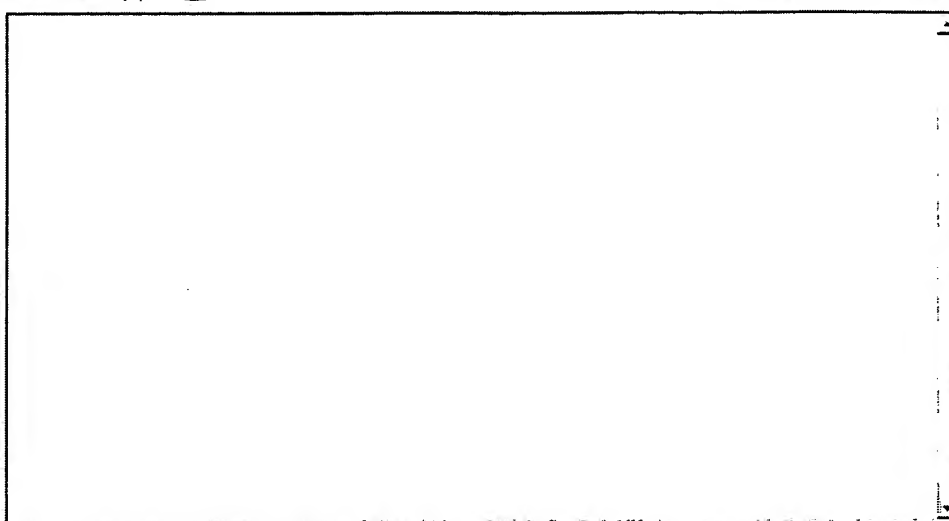 - L1: (55) (electron near2 emission) and (electrode near:
  - L2: (33) 1 and (semiconductor near2 (layer or film or c
  - L3: (33) 2 and (voltage or potential)
  - L5: (73) 4 and (semiconductor near2 (layer or film or c
  - L6: (71) 5 and (voltage or potential)
  - L14: (128) 4 and (voltage or potential)
  - L4: (132) (electron near2 emiS5) and (electrode near2
  - L31: (4979) (electron near2 emiS5) and electrode and
  - L32: (20) 31 and (cleaning near2 functionS3)
  - L33: (452) (electron near2 emiS5) and (electrode near
  - L34: (70) 33 and (counter adj electrode)
  - L36: (27) (electron near2 emiS5) and (electrode near2
  - L35: (691) (electron near2 emiS5) and (electrode near
- Failed
- Saved
- Favorites
- Tagged (0)
- UDC
- Queue
- Trash

Search   List   Browse   Queue   Clear

DBs   US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB

Default operator: OR

☑ Plurals
☑ Highlight all hit terms initially

BRS form   IS&R form   Image   Text   HTML

	Type	L #	Hits	Search Text	DBs	Time Stamp	C	Er	Erro
1	BRS	L1	55	(electron near2 emission) and (electrode near2 (lower and upper and counter))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
2	BRS	L2	33	1 and (semiconductor near2 (layer or film or coatS3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
3	BRS	L3	33	2 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
4	BRS	L5	73	4 and (semiconductor near2 (layer or film or coatS3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
5	BRS	L6	71	5 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:11			
6	BRS	L14	128	4 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:24			
7	BRS	L4	132	(electron near2 emiS5) and (electrode near2 (lower and upper and counter))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:34			
8	BRS	L31	4979	(electron near2 emiS5) and electrode and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:38			
9	BRS	L32	20	31 and (cleaning near2 functionS3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:36			
10	BRS	L33	452	(electron near2 emiS5) and (electrode near2 (upper and lower)) and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:48			
11	BRS	L34	70	33 and (counter adj.electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:44			
12	BRS	L36	27	(electron near2 emiS5) and (electrode near2 (upper and lower and counter)) and "313"/S.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:49			
13	BRS	L35	691	(electron near2 emiS5) and (electrode near2 (upper and lower)) and "313"/S.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:50			

Hits   Details   HTML

Ready